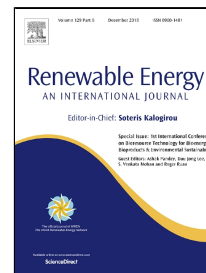


# Accepted Manuscript

An overview of ultra-refractory ceramics for thermodynamic solar energy generation at high temperature



Laura Silvestroni, Diletta Sciti, Luca Zoli, Andrea Balbo, Federica Zanotto, Roberto Orrù, Roberta Licheri, Clara Musa, Luca Mercatelli, Elisa Sani

PII: S0960-1481(18)30986-8  
DOI: 10.1016/j.renene.2018.08.036  
Reference: RENE 10463  
To appear in: *Renewable Energy*  
Received Date: 21 March 2018  
Accepted Date: 09 August 2018

Please cite this article as: Laura Silvestroni, Diletta Sciti, Luca Zoli, Andrea Balbo, Federica Zanotto, Roberto Orrù, Roberta Licheri, Clara Musa, Luca Mercatelli, Elisa Sani, An overview of ultra-refractory ceramics for thermodynamic solar energy generation at high temperature, *Renewable Energy* (2018), doi: 10.1016/j.renene.2018.08.036

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.

1           **An overview of ultra-refractory ceramics for thermodynamic solar energy**  
2                           **generation at high temperature**  
3

4   Laura Silvestroni<sup>1</sup>, Diletta Sciti<sup>1\*</sup>, Luca Zoli<sup>1</sup>, Andrea Balbo<sup>1,2</sup>, Federica Zanutto<sup>2</sup>, Roberto Orrù<sup>3</sup>,  
5   Roberta Licheri<sup>3</sup>, Clara Musa<sup>3</sup>, Luca Mercatelli<sup>4</sup>, Elisa Sani<sup>4</sup>

6  
7   <sup>1</sup>CNR-ISTEC, Institute of Science and Technology for Ceramics, Via Granarolo 64, I-48018 Faenza  
8   (Italy);

9   <sup>2</sup>Corrosion and Metallurgy Study Centre “Aldo Daccò”, Engineering Department, University of  
10   Ferrara, G. Saragat 1, Ferrara 44122, Italy;

11   <sup>3</sup>Mechanical Engineering, Chemistry and Materials Department, University of Cagliari, via Marengo  
12   2, Cagliari 09123, Italy;

13   <sup>4</sup>CNR-INO, National Institute of Optics, Largo E. Fermi, 6, I-50125 Firenze, Italy;

14  
15   \*corresponding author: [diletta.sciti@istec.cnr.it](mailto:diletta.sciti@istec.cnr.it), ISTEC-CNR, Faenza, Italy

16  
17           **ABSTRACT**

18           An efficiency improvement of concentrating solar power systems relies on a significant increase  
19   of the operating temperatures, exceeding 600°C. This goal can be achieved through the use of solar  
20   absorbers possessing high spectral selectivity and stability at such temperatures. Suitable alternatives  
21   to the largely used silicon carbide can be found in the ultra-high temperature ceramics class. This  
22   study focuses on the effect of processing, microstructure evolution and surface texture on the optical  
23   properties at room and high temperature. ZrB<sub>2</sub>-based ceramics are taken as case study to detect any  
24   correlation amongst composition, porosity, mean grain size, roughness and spectral selectivity. In  
25   addition, the effect of surface variation, induced by chemical etching or by exposure to oxidizing  
26   environment, thus simulating the actual operation conditions, are evaluated and compared to SiC

27 optical properties. Absorbance and solar selectivity are discussed as a function of the microstructural  
28 and surface properties upon detailed roughness characterization. Advantages in the use of UHTC as  
29 solar absorbers, strength and criticalities related to the use of these ceramics in comparison with SiC  
30 are discussed.

31

32 **Keywords:** Ultra-High Temperature Ceramics;  $ZrB_2$ ; optical properties; solar absorbers;  
33 concentrating solar power, ageing.

34

35

## 36 1. Introduction

37 The worldwide growing concern with environmental preservation has forced changes in energy  
38 management, promoting the pursuit of new technologies for energy production. In addition, as the  
39 world's population is expected to expand, the demand for energy will grow as well. Hence, the use  
40 of clean, safe and cost-effective energy supplies, such as solar energy, will have a fundamental role  
41 within the global social and economic framework. Concentrating Solar Power (CSP) technology is a  
42 safe, sustainable and cost-effective energy supply [1–5]. In CSP technology, the heat absorbed on the  
43 collector material is transferred to a heat transfer fluid, which plays a very vital role in determining  
44 the overall efficiency of solar energy utilization. The efficiency of solar thermal power plants indeed  
45 increases rapidly with increasing working temperatures. Currently, the typical temperatures achieved  
46 in solar towers are around  $565^\circ\text{C}$  when molten salts are used as heat transfer fluid, but may exceed  
47  $600^\circ\text{C}$  on the tube outer surface [6]. Only in few cases, in open volumetric air receivers, direct heating  
48 of air is also being reported to achieve very high temperatures approximating  $800^\circ\text{C}$  [7–9]. In any  
49 case, to improve the competitiveness of this power generation technology, the receiver performance  
50 has to be improved, particularly its stability at high temperatures.

51 In the framework of the Italian project SUPERSOLAR (<http://www.ino.it/supersolar>), ceramic  
52 materials aimed to be used as absorbers in thermal solar energy plants operating at temperatures  
53 higher than current systems have been investigated and developed.

54 Diborides and carbides of zirconium, hafnium and tantalum ( $ZrB_2$ ,  $ZrC$ ,  $HfB_2$ ,  $HfC$ ,  $TaB_2$ ,  $TaC$ ),  
55 referred to as Ultra-High-Temperature-Ceramics (UHTCs), are considered the best-emerging  
56 materials for applications in aerospace and advanced energy systems (turbine blades, combustors,  
57 scramjet engines, nuclear fusion reactors) [10]. The increasing interest in these materials is due to  
58 their unique combination of properties, including the highest melting points of any group of materials,  
59  $>3000^\circ\text{C}$ , elevate strength at extreme temperature, like 600-800 MPa at  $1500\text{-}2100^\circ\text{C}$  [11], high  
60 thermal conductivity, 80-110 W/mK up to  $2000^\circ\text{C}$  [12] and chemical stability. Recently, it has been  
61 found that most of these compounds also have the characteristic of being intrinsic solar selective  
62 materials [13–19], but the understanding of the optical properties of these materials is still very scanty,  
63 especially at high temperature. UHTCs have thus the potential to be suited for application in high  
64 temperature solar receivers, once their basic properties have been properly investigated and correlated  
65 to the bulk and surface characteristics.

66 The main objective of SUPERSOLAR project was to systematically study the UHTC fundamental  
67 optical properties, i.e. light absorption and emission at room and high temperatures. Particular  
68 emphasis was devoted to identify their correlation with relevant material characteristics, such as  
69 compositions, porosity, surface finishing. Several ultra-refractory boride and carbides have been  
70 studied in the framework of the project [13–17], allowing to identify the most promising materials  
71 for solar absorber applications. This work describes, as a case study, an extensive work on  $ZrB_2$ -  
72 based ceramics, consolidated through different processes, with or without  $MoSi_2$  as secondary phase,  
73 textured or with controlled porosity. Among UHTC materials,  $ZrB_2$  was selected for broad  
74 characterization in view of a number of advantages on several aspects: borides possess better thermo-  
75 mechanical properties and higher oxidation resistance than carbides [10,20], it has lower weight than

76 other transition metals compounds, around 6 g/cm<sup>3</sup> compared to 11-12 g/cm<sup>3</sup> for Hf- or 11-14 g/cm<sup>3</sup>  
77 for Ta- based compounds, and, least but not last, ZrB<sub>2</sub> is the cheapest raw powder in this class.  
78 The literature shows several reports about the mechanical property changes of ZrB<sub>2</sub> as a function of  
79 different processing parameters [20–24], while, to the best of our knowledge, the impact on optical  
80 properties has been not investigated yet. For the preparation of the ZrB<sub>2</sub>-based composites, MoSi<sub>2</sub>  
81 was selected in this work as sintering additive in view of its properties compatible with the high-  
82 temperature environment, i.e. melting point above 2000°C, high stiffness [25] and owing to its  
83 beneficial effects on densification, high temperature strength and oxidation resistance improvement  
84 of borides [20,26].

85 The effect of microstructural and surface features is then correlated to the optical absorbance and  
86 spectral selectivity. In addition, the optical properties of these ceramics exposed to oxidizing  
87 environment, simulating the prolonged use in air at high temperature, are discussed and compared to  
88 the performances of the currently used absorber materials, mostly based on silicon carbide (SiC).  
89 Finally, high temperature spectral emittance spectra of ZrB<sub>2</sub> composites are shown and compared to  
90 that of SiC.

91

## 92 **2. Materials and Methods**

### 93 **2.1 Materials preparation and characterization**

94 *Spark plasma sintered material.* A bulk pure ZrB<sub>2</sub> material was prepared starting from Self  
95 propagating High-temperature Synthesized (SHS) powders and consolidated by spark plasma  
96 sintering (SPS), sample ZBM0-s, according to the procedure reported in [27]. Briefly, before being  
97 consolidated, the SHS product received a mild ball milling treatment to generate powders with an  
98 average particles size of 6.7 μm and d<sub>90</sub> parameter value of 16.8±1.0 μm. The SPS process was  
99 conducted using a 515S model equipment (Fuji Electronic Industrial Co., Ltd., Kanagawa, Japan)  
100 under vacuum (20 Pa) conditions.

101 *Hot pressed materials.* ZrB<sub>2</sub>-composites containing MoSi<sub>2</sub> were prepared using commercial raw  
102 powders: ZrB<sub>2</sub> (H. C. Starck, Germany. Grade B), mean particle size: 1.5 μm, impurities (wt%): C  
103 0.25, O 2.0, N 0.25, Fe 0.1, Hf 0.2; MoSi<sub>2</sub> (Aldrich, Milwaukee, USA), mean particle size: 2.8 μm,  
104 impurities (wt%): O 1.0. The amount of sintering agent ranged from 5 to 50 vol% to enable full  
105 densification and labeled hereafter as ZBMX, where X = 5, 10, 20, 30, 50. The mixtures were  
106 prepared by wet milling for 24 h using absolute ethanol and SiC milling media, followed by drying  
107 in a rotary evaporator and sieving through 250 μm screen. 30 mm diameter green pellets were  
108 prepared by uniaxial pressing with 20 MPa. Hot pressing was performed in low vacuum (~100 Pa)  
109 using an induction-heated graphite die at temperatures between 1750 and 1900°C with an uniaxial  
110 pressure of 30 MPa during heating and a dwell at the maximum temperature set on the basis of the  
111 shrinkage curve, as reported in Table I.

112 *Pressureless materials:* ZrB<sub>2</sub>-composites containing 20 vol% MoSi<sub>2</sub> were sintered in a graphite  
113 furnace (Astro industries Inc., Santa Barbara, USA) without applied pressure, with a heating rate of  
114 600°C/h under flowing argon atmosphere (~0.1 MPa) at 1950°C for 60 minutes, as indicated in Table  
115 I, sample ZBM20-ps. Additionally, for high temperature emittance measurements, one 40-mm  
116 diameter pellet with 10 vol% MoSi<sub>2</sub> and with a pore-forming agent, ZBM10P, was prepared and  
117 pressureless sintered in the same graphite furnace at 1950°C reaching a relative final density of 87%.

118 *Texture modification and ageing:* Surface texture modifications were induced by chemical etching  
119 in order to improve the solar radiation absorption. In particular, the polished surface of ZBM10  
120 samples was exposed to a mixture of mineral acid (HF/HNO<sub>3</sub>) for few seconds, thereafter labelled as  
121 ZBMetc.

122 In addition, the effect of prolonged exposure to high temperatures was evaluated by oxidation of  
123 the same composition in air furnace at 800 and 1200°C for 10 hours (Nannetti 1700°C, mod. FH 65/17,  
124 Faenza, Italy). The resulting oxidized surfaces were labelled as ZBM800 and ZBM1200.

125 For the as-sintered materials, the bulk densities were measured by Archimedes' method in distillate  
126 water according to the ASTM C373-88 standard and the microstructure was analyzed on polished or

127 treated surfaces by scanning electron microscopy (FE-SEM, Carl Zeiss Sigma NTS GmbH,  
128 Oberkochen, DE) and energy dispersive x-ray spectroscopy (EDS, INCA Energy 300, Oxford  
129 instruments, UK). The optical surface of the pellets were polished by diamond paste with decreasing  
130 grain size, from 30 to 1  $\mu\text{m}$  using a standard procedure. Quantitative calculations of the  
131 microstructural parameters, like residual porosity, mean grain size and secondary phase content, were  
132 carried out via image analysis with a commercial software package (Image-Pro Plus® version 7,  
133 Media Cybernetics, Silver Springs, MD, USA).

134 The surface texture characterization was carried out with a non-contact optical profilometer  
135 (Taylor-Hobson CCI MP, Leicester, UK) equipped with a green light and a 20X magnification  
136 objective lens. For each samples, at least two distinct areas ( $0.8 \times 1 \text{ cm}^2$ ) were scanned along two  
137 orthogonal directions and the collected surface data were processed with the Talymap 6.2 software  
138 (Taylor-Hobson, Leicester, UK). The analysis of surface data was carried out in terms of areal field  
139 parameters, as 3D parameters can provide a more comprehensive information about surface texture  
140 with respect to 2D ones. The evaluation of 3D texture parameters was performed following the ISO  
141 25178-2:2012 standard on the two datasets collected for each sample, after denoising (median filter  
142  $5 \times 5$ ), form removing and filtering with an aerial robust gaussian L-filter.

143

## 144 **2.2 Methods and parameters for optical characterization**

145 The parameters selected to qualify the materials were hemispherical reflectance, high temperature  
146 emittance and spectral selectivity.

147 - Hemispherical reflectance spectra were acquired using two instruments: a double-beam  
148 spectrophotometer (Perkin Elmer Lambda900) equipped with a Spectralon®-coated  
149 integration sphere for the 0.25-2.5  $\mu\text{m}$  wavelength region and a Fourier Transform  
150 spectrophotometer (FT-IR Bio-Rad "Excalibur") equipped with a gold-coated integrating  
151 sphere and a liquid nitrogen-cooled detector for the range 2.5-16.5  $\mu\text{m}$ .

- 152 - High temperature emittance spectra were obtained as the ratio between the radiance emitted  
 153 by the sample heated in a home-made high-vacuum furnace (ultimate pressure limit few  $10^{-6}$   
 154 mbar, maximum temperature around 1200K), and that emitted by a reference blackbody (C.I.  
 155 Systems SR-2) at the same temperature. Radiances were detected and spectrally resolved by  
 156 the FT-IR "Excalibur" spectrophotometer described above. Details of the experimental  
 157 apparatus can be found in [28]. The available spectral range for high temperature emittance  
 158 measurements was between 2 and 21  $\mu\text{m}$  wavelength.
- 159 - As a third evaluation parameter, spectral selectivity was calculated as the ratio between the  
 160 total solar absorbance,  $\alpha$ , and the estimated hemispherical emittance,  $\varepsilon$ .  $\alpha$ , is given, in terms of  
 161 the experimental room-temperature hemispherical reflectance  $\rho^{\wedge}(\lambda)$ , by the following  
 162 expression:

$$\alpha = \frac{\int_{\lambda_{\min}}^{\lambda_{\max}} (1 - \rho^{\wedge}(\lambda)) \cdot S(\lambda) d\lambda}{\int_{\lambda_{\min}}^{\lambda_{\max}} S(\lambda) d\lambda} \quad (1)$$

164 where  $S(\lambda)$  is the Sun emission spectrum [29] and the integration is carried out between  $\lambda_{\min}=0.3 \mu\text{m}$   
 165 and  $\lambda_{\max}=2.3 \mu\text{m}$ . The estimated hemispherical emittance,  $\varepsilon$ , at the temperature of 1200 K, taken as  
 166 hypothetical working temperature of a future solar absorber, was determined as follows:

$$\varepsilon = \frac{\int_{\lambda_1}^{\lambda_2} (1 - \rho^{\wedge}(\lambda)) \cdot B(\lambda, 1200K) d\lambda}{\int_{\lambda_1}^{\lambda_2} B(\lambda, 1200K) d\lambda} \quad (2)$$

168 where  $B(\lambda, 1200K)$  is the blackbody spectral radiance at 1200K temperature and the integration is  
 169 carried out in the interval  $\lambda_1=0.3 \mu\text{m}$ -  $\lambda_2=16.0 \mu\text{m}$ .

170

### 171 3. Results

#### 172 3.1 Microstructure



173 *Polished surfaces* - To correlate the optical spectra to compositional characteristics, SEM/EDS  
 174 characterization was carried out on the optically investigated surfaces. All spark plasma sintered and  
 175 hot pressed ceramics achieved density above 95%, Table I. Examples of the microstructures obtained  
 176 are displayed in Fig. 1 a-d. The combination of the SHS method with the SPS technique allowed for  
 177 the obtainment of an additive-free  $ZrB_2$  product, ZBM0-s, with relatively high density level, Fig. 1a  
 178 and Table I. The use of high mechanical pressures, 60 MPa, contributed to such achievement [27].

Label	MoSi <sub>2</sub> vol%	Sintering technique	T,t,P °C, min, MPa	Bulk relative density %	Surface porosity vol%	Mean pore size µm	Mean g.s. µm	Max g.s. µm	Min g.s. µm	Secondary phases by SEM-EDS vol%
ZBM0-s	0	SPS	1850,20,60	>96	~4	4.90	19±6	33.5	8.5	-
ZBM5	5	HP	1900,10,30	>98	~2	0.13	1.9±0.7	3.6	0.9	1.4 MoSi <sub>2</sub> , 1.5 SiO <sub>2</sub> /SiC
ZBM10	10	HP	1850,10,30	>96	~4	0.13	2.4±0.6	3.9	1.4	8.5 MoSi <sub>2</sub> , 1.4 SiO <sub>2</sub> , 0.7 SiC
ZBM20	20	HP	1800,4,30	>98	~2	0.10	2.4±0.9	5.4	0.6	13 MoSi <sub>2</sub> , 2.5 SiO <sub>2</sub> , 2.0 SiC, 0.7 ZrO <sub>2</sub> , 0.6 MoB
ZBM30	30	HP	1850,3,30	>98	~2	0.10	1.7±0.6	3.6	0.6	28.4 MoSi <sub>2</sub> , 3.4 SiO <sub>2</sub> /SiC
ZBM50	50	HP	1750,13,30	>98	~2	0.10	1.9±0.8	4.3	0.7	39 MoSi <sub>2</sub> , 6.5 SiO <sub>2</sub> , 2 MoB, 1 ZrO <sub>2</sub> , 1 SiC
ZBM20-ps	20	PS	1950,60,-	>98	~2	1.45	2.6±0.7	1.3	4.1	18 MoSi <sub>2</sub> , 2 MoB, 0.5 SiO <sub>2</sub>
ZBM10P	10	PS	1950,60,-	~87	~13	4.70	2.8±0.7	5.2	1.2	8 MoSi <sub>2</sub> , 2 MoB

179 Table I: Composition, sintering technique and parameters, T: maximum temperature, t: dwell at T, P: applied pressure,  
 180 relative density, porosity features, mean, maximum and minimum grain size (g.s.) and secondary phases of the  $ZrB_2$ -  
 181 based materials. Porosity is estimated by image analysis. SPS: spark plasma sintering, HP: hot pressing, PS: pressureless  
 182 sintering.

183  
 184 Nonetheless, Fig. 1a shows that about 4 vol% residual rounded closed porosity, with mean size  
 185 around 4.9 µm, remained trapped within  $ZrB_2$  grains. In addition, the latter ones display quite larger  
 186 dimensions, around 20 µm, with the maximum size being up to 34 µm. This outcome is likely a  
 187 consequence of the relatively coarser SHS powders used for SPS experiments with respect to  
 188 commercial raw  $ZrB_2$  material alternatively utilized in the present study, i.e. 6.7 µm and 2.8 µm mean  
 189 sizes, respectively.

190 Finer starting powder and the addition of MoSi<sub>2</sub> enabled to reduce surface porosity in the sintered  
 191 samples, when using either a pressureless oven or a hot pressing furnace, Table I.

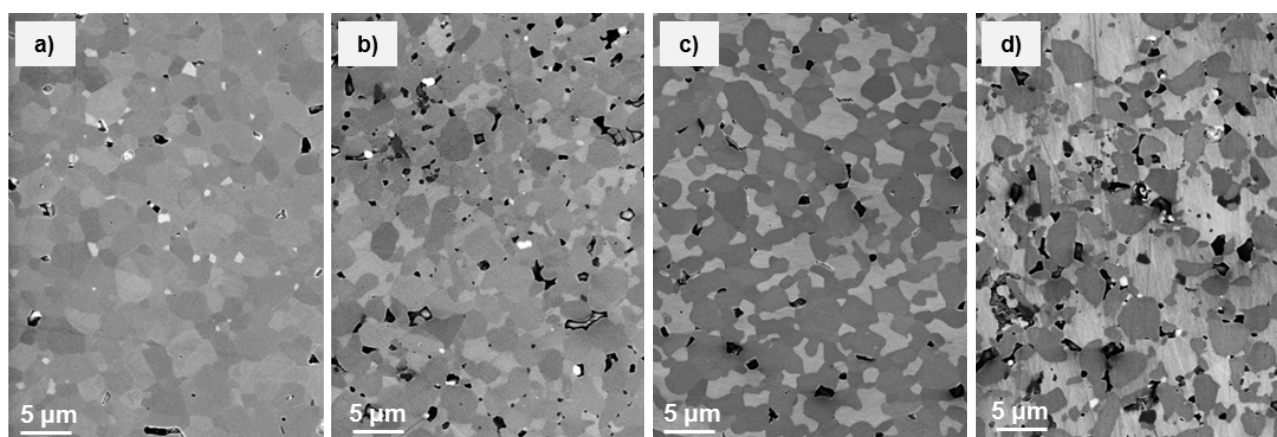
192 In Fig. 1b,c and Fig.2  $ZrB_2$  exhibits rounded grey grains, while MoSi<sub>2</sub> is characterized by brighter  
 193 contrast and an irregular shape with low dihedral angles. Beside MoSi<sub>2</sub> we observed silica pockets

194 recognizable as dark contrasting phases, often embedding small SiC grains, ZrO<sub>2</sub> and MoB.  
195 Formation of these phases during sintering at high temperature is due to MoSi<sub>2</sub> reaction with oxygen  
196 coming from B<sub>2</sub>O<sub>3</sub> present on boride particles surface and subsequent formation of SiO<sub>2</sub> and MoB  
197 [20]. Silica is often partially reduced to SiC, due to abundancy of C in graphite-based furnaces.  
198 Secondary phases are listed in Table I and, as a consequence of these reactions, the final effective  
199 MoSi<sub>2</sub> content in the materials containing MoSi<sub>2</sub> is slightly different from the nominal one. The  
200 matrix mean grain size of the hot pressed ZBMX materials, whose microstructure overview is  
201 displayed in Fig. 2, slightly decreased with increasing MoSi<sub>2</sub> content, whilst the pores dimension did  
202 not notably vary, being around 0.10-0.13 μm, Table I. The grain size is influenced both by decreased  
203 sintering temperature, 1900°C for ZBM5 and 1750°C for ZBM50, and by the distribution of MoSi<sub>2</sub>,  
204 which, at high volume fraction, hindered ZrB<sub>2</sub> grains coalescence by creating a continuous  
205 interpenetrating network within the boride skeleton, thus obstructing mass transfer. Porosity and  
206 mean grain size reduction through MoSi<sub>2</sub> addition leads on one side to increased mechanical  
207 properties [20], but on the other side spectral selectivity worsens almost linearly with increasing  
208 MoSi<sub>2</sub>, as discussed later.

209 Fig. 1: SEM images of the surface of various ZrB<sub>2</sub>-based ceramics showing different microstructural features. a) ZBM0-s  
210 by SHS/SPS, b) ZBM20-ps by pressureless sintering; c) ZBM10 by HP and d) porous ZBM10P by pressureless sintering  
211 in presence of pore-generating agent. Pores are marked with dotted circles.

212

213 The material produced with the addition of a pore-forming agent ZBM10P, had a surface  
214 porosity around 13-15 vol% and displayed a very irregular surface with pore sizes around 3-7 μm,  
215 Fig. 1d. The same secondary phases were recognized as for the dense composites produced by hot  
216 pressing.

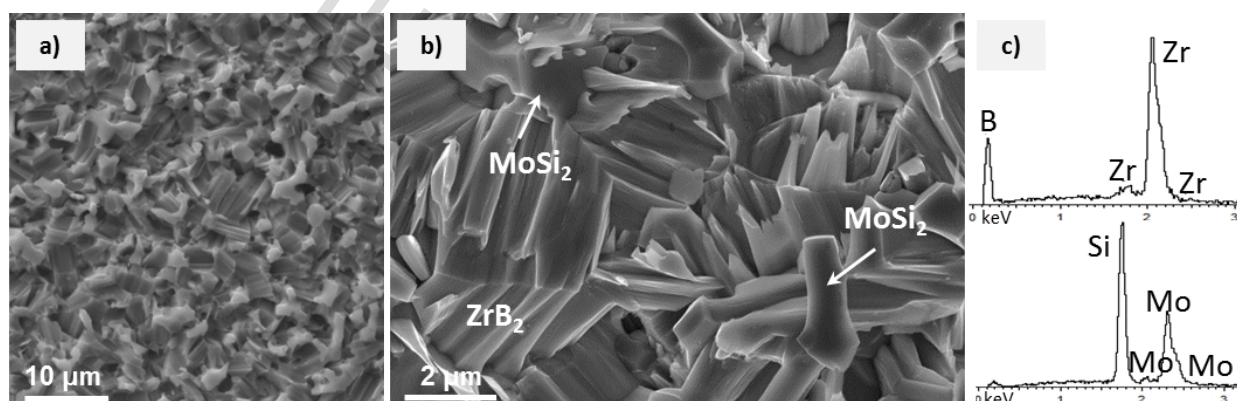


217

218 Fig. 2: SEM images of the polished surfaces of hot pressed  $ZrB_2$ -based composites with increasing  $MoSi_2$  amount: a) 5  
 219 vol%, b) 20 vol%, c) 30 vol% and d) 50 vol%.

220

221 *Etched surface* - To increase the capability to trap solar radiation, chemical etching was performed  
 222 in a  $HNO_3/HF$  solution on the ZBM10 sample. X-ray diffraction analysis on the chemically etched  
 223 surface (not shown), ZBMe<sub>tc</sub>, revealed that only hexagonal  $ZrB_2$  and tetragonal  $MoSi_2$  were indexed,  
 224 with no additional oxides or reaction products formed upon the chemical corrosion. The  
 225 microstructure of the etched surface is reported in Fig. 3. It can be seen that the chemical treatment  
 226 effectively etched the surface creating faceted acicular  $ZrB_2$  grains, while leaving  $MoSi_2$  unchanged  
 227 with its pristine smooth contours (compare Fig. 1c and Fig. 3a). Noteworthy, the phase composition  
 228 did not undergo modification and no contamination by oxygen, fluorine or nitrogen was detected on  
 229 the etched surface, as demonstrated by the EDS spectra reported in Fig. 3c.



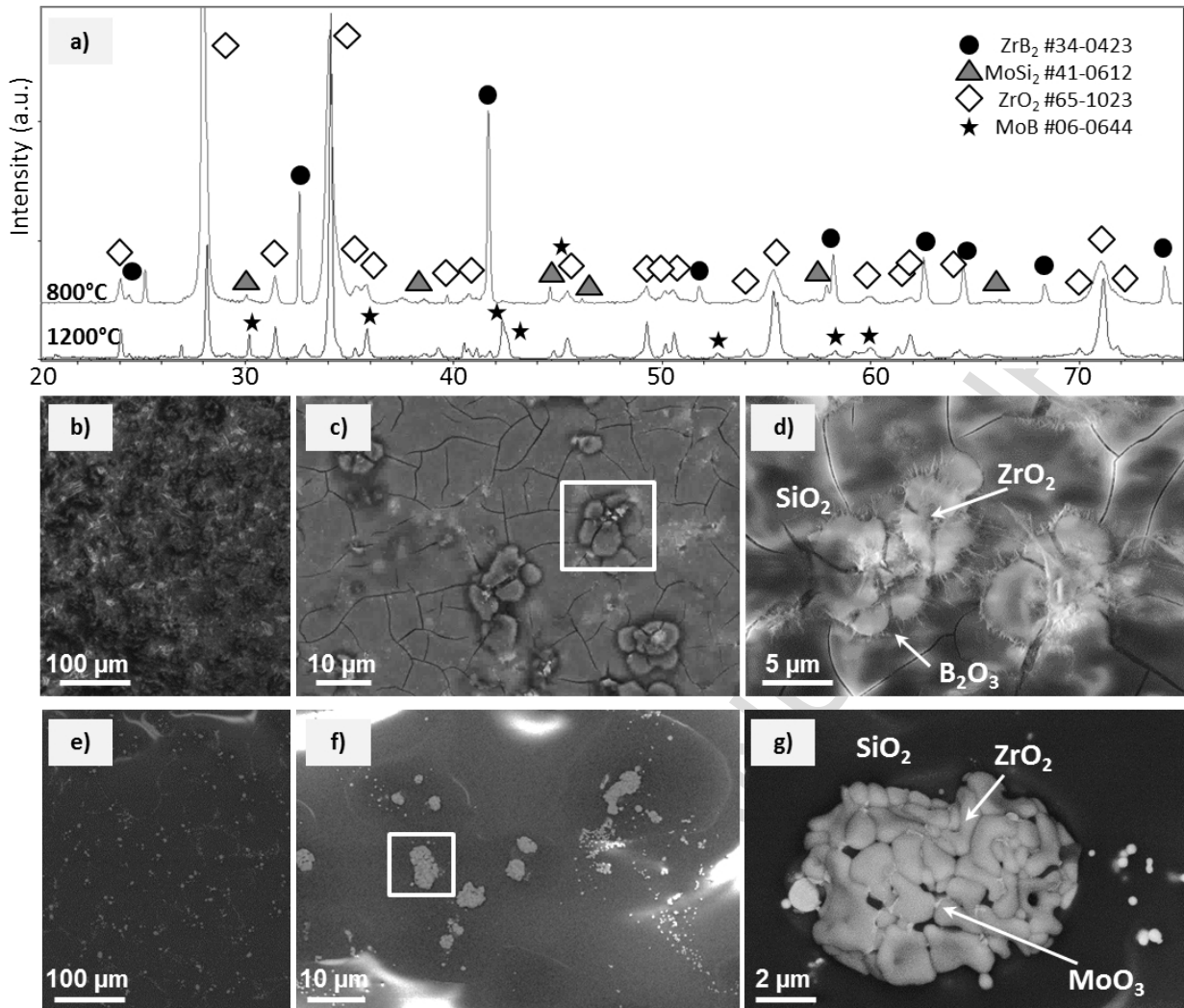
230

231 Fig. 3: a)-b) SEM images of the chemically etched surface of ZBM10 with corresponding EDS spectra in c).

232

233 *Oxidized surfaces* - The oxidized ZBM10 samples showed a remarkably changed surface with a  
234 glassy appearance. The X-ray diffraction patterns after oxidation at 800 and 1200°C are reported in  
235 Fig. 4a. At the lowest temperature, the crystalline phases detected are monoclinic ZrO<sub>2</sub>, the pristine  
236 ZrB<sub>2</sub> and MoSi<sub>2</sub>, whilst tetragonal MoB is found instead of ZrB<sub>2</sub> when the oxidation process was  
237 conducted at the highest thermal level. To note that a preferential orientation of ZrO<sub>2</sub> phase along the  
238 [002] planes at 2θ=34° took place upon exposure at 1200°C, instead of preserving the nominal peak  
239 intensity 100% corresponding to the [-111] planes at 2θ=28°. Future optical measurements will show  
240 if this change of grains orientation has an impact on the solar absorbance.

241 SEM images of the oxidized surfaces are shown in Fig. 4b-g. At 800°C, Fig. 4b-d, the sample is  
242 covered by a continuous boro-silicate glassy layer, which incorporates B<sub>2</sub>O<sub>3</sub> crystals and bright ZrO<sub>2</sub>  
243 agglomerates, 10-20 μm sized. Cracks in the glass are presumably formed upon cooling. At 1200°C,  
244 Fig. 4e-g, the outer scale is mainly based on silica, without boron traces, and contains about 5 μm-  
245 sized ZrO<sub>2</sub> agglomerates, where the MoO<sub>3</sub> phase, with white contrast, is disposed intergranularly,  
246 Fig. 4g.



247

248 Fig. 4: a) X-ray diffraction patterns of ZBM10 upon exposure to oxidizing environment at 800°C and 1200°C for 10 hours  
 249 and corresponding SEM images of the external surface oxidized at b)-d) at 800°C and e)-g) 1200°C. d) and g) are  
 250 magnified images of the boxed areas in c) and f), respectively.

251

### 252 3.2 Surface texture characterization

253 The surface texture has significant effects on surface absorbance and reflectance, therefore, in  
 254 order to investigate the intrinsic optical properties of the synthesized materials and evaluate the  
 255 contributions arising from surface texturing treatment, each sample was characterized from a  
 256 topological point of view before performing optical measurements.

257 The surface texture was characterized by evaluating the areal height parameters (Sa, Sq, Ssk,  
 258 Sku, Sp, Sv and Sz) on the L-filter surface. These parameters provide useful information about the

259 optical characteristics of a surface, indeed,  $S_a$  is related to the surface roughness,  $S_q$  to the way in  
260 which light is scattered from a surface, while  $S_{sk}$  and  $S_{ku}$  are correlated to the type of defects and to  
261 their distribution on the samples surface. In particular, negative values of  $S_{sk}$  indicate the  
262 predominance of pores or valleys, while large and positive values ( $> 3$ ) of  $S_{ku}$  indicate the presence  
263 of a certain amount of high peaks or deep valleys/pores. [30].

264 In Table 2 the average values of the areal height parameters measured on the studied samples,  
265 along with the corresponding standard deviation, are reported.

266 With the exception of ZBM800, ZBM1200, all the tested specimens showed negative values of  $S_{sk}$   
267 and values of  $S_{ku}$  higher than 3. This result indicates that the surface of these samples is characterized  
268 by the presence of comparatively few peaks and by the prevalence of quite pronounced pores or  
269 valley. These findings are in agreements with the higher values of  $S_v$  with respect of  $S_p$  detected on  
270 these samples. This surface morphology can induce significant improvements to the surface  
271 absorbance since it can trap the incident photons and promote their absorption through multiple  
272 reflections along the walls of the pore or valley. The relatively high dispersion measured on  $S_{sk}$  and  
273  $S_{ku}$  is related to the fact these parameters are very sensitive to surface defects since, in their  
274 mathematical expression, high order powers of surface heights are used.

275  $S_a$  and  $S_q$  values for the  $ZrB_2$ -based composites follow similar trend on all the tested  
276 materials. In particular, hot pressed and pressureless sintered materials showed comparable values of  
277 both these parameters. Small variations observed are probably due to differences in surface finishing  
278 obtained on samples with different composition.

279 Higher values of  $S_a$  and  $S_q$  measured on SPS are probably due to the higher surface porosity (4%)  
280 observed on this sample. When the bulk porosity increases over 10%, in the case of ZBM10P, and  
281 the porosity changed from close to open, the surface becomes very rough and  $S_a$  and  $S_q$  increase  
282 accordingly about 2 orders of magnitude.

283 The chemical etching induced significant surface modifications on ZBM10, as highlighted in  
284 Figure 3. On ZBMetc, both  $S_a$  and  $S_q$  increased more than one order of magnitude in comparison

285 with the polished ZBM10 sample while the Ssk and Sku parameters showed a slight decrease in  
 286 absolute values indicating a bumpy surface morphology.

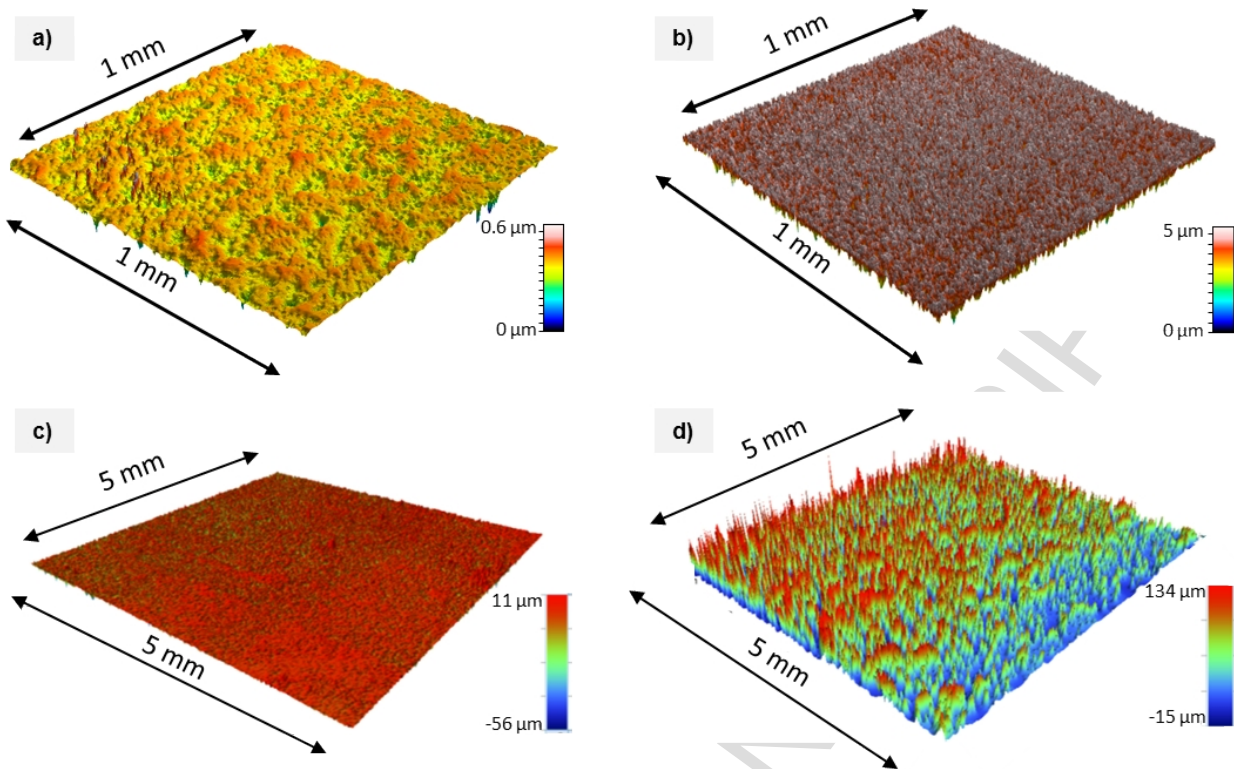
287

	Polished							Porous	Etched	Oxidised	
	ZBM0-s	ZBM5	ZBM10	ZBM20	ZBM30	ZBM50	ZBM20-ps			ZBM10-P	ZBM Etc
<i>Sq</i> ( $\mu\text{m}$ )	0.44±0.10	(68±4)·10 <sup>-3</sup>	(34±3)·10 <sup>-3</sup>	(12±3)·10 <sup>-3</sup>	(16±1)·10 <sup>-3</sup>	(22±1)·10 <sup>-3</sup>	(37±10)·10 <sup>-3</sup>	1.72±0.02	0.69±0.01	0.5±0.3	5.6±4.3
<i>Ssk</i>	-7.1±1.1	-2.4±0.7	-1.2±0.5	-4.5±2.1	-3.8±0.4	-6.1±1.6	-6.7±1.2	-4.3±0.1	-0.7±0.1	0.9±2.4	1.1±0.9
<i>Sku</i>	83±15	12±4	8±3	81±60	36±5	80±40	97±28	16.3±0.6	3.3±0.6	29±12	5.9±1.6
<i>Sp</i> ( $\mu\text{m}$ )	0.8±0.1	5.9±3.5	0.27±0.01	0.21±0.15	0.21±0.01	0.21±0.01	0.28±0.01	8.4±2.9	3.0±1.7	9.8±2.6	46±33
<i>Sv</i> ( $\mu\text{m}$ )	9.6±2.5	4.1±2.7	0.51±0.18	0.63±0.46	0.44±0.04	0.70±0.20	1.47±0.74	25.3±0.2	5.5±1.5	9.3±10	11.6±1.1
<i>Sz</i> ( $\mu\text{m}$ )	10.4±2.7	10.1±3.1	0.8±0.2	0.8±0.6	0.66±0.04	0.9±0.2	1.8±0.7	33.6±3.3	8.5±3.1	19.1±8.8	57±34
<i>Sa</i> ( $\mu\text{m}$ )	0.21±0.28	(33±4)·10 <sup>-3</sup>	(25±2)·10 <sup>-3</sup>	(8±2)·10 <sup>-3</sup>	(100±1)·10 <sup>-4</sup>	(12±1)·10 <sup>-3</sup>	(17±4)·10 <sup>-3</sup>	1.16±0.01	0.57±0.01	0.36±0.18	4.2±3.2

288 Table II: Measured average values and standard deviation of 3D surface texture parameters of the polished and textured  
 289 (porous/etched/oxidized) ZrB<sub>2</sub>-based composites.

290

291 In the case of oxidized samples, a completely different surface morphology was observed. The  
 292 presence of large and irregular oxidation products, fashioned a surface texture characterized by the  
 293 prevalence of high irregular peaks in agreement with high values of Sq and Sa and with the positive  
 294 values of Ssk and Sku parameters. For a more immediate and straightforward comparison, topography  
 295 maps of the pristine and treated surface are shown in Fig. 5.



296

297 Fig. 5: Topographic maps of the ZBM10 sample upon different surface finishing a) as-polished, b) chemically etched  
 298 (ZBMetc), c) oxidized at 800°C (ZBM800) and d) oxidised at 1200°C (ZBM1200) for 10 hours.

299

### 300 3.4 Optical characterization

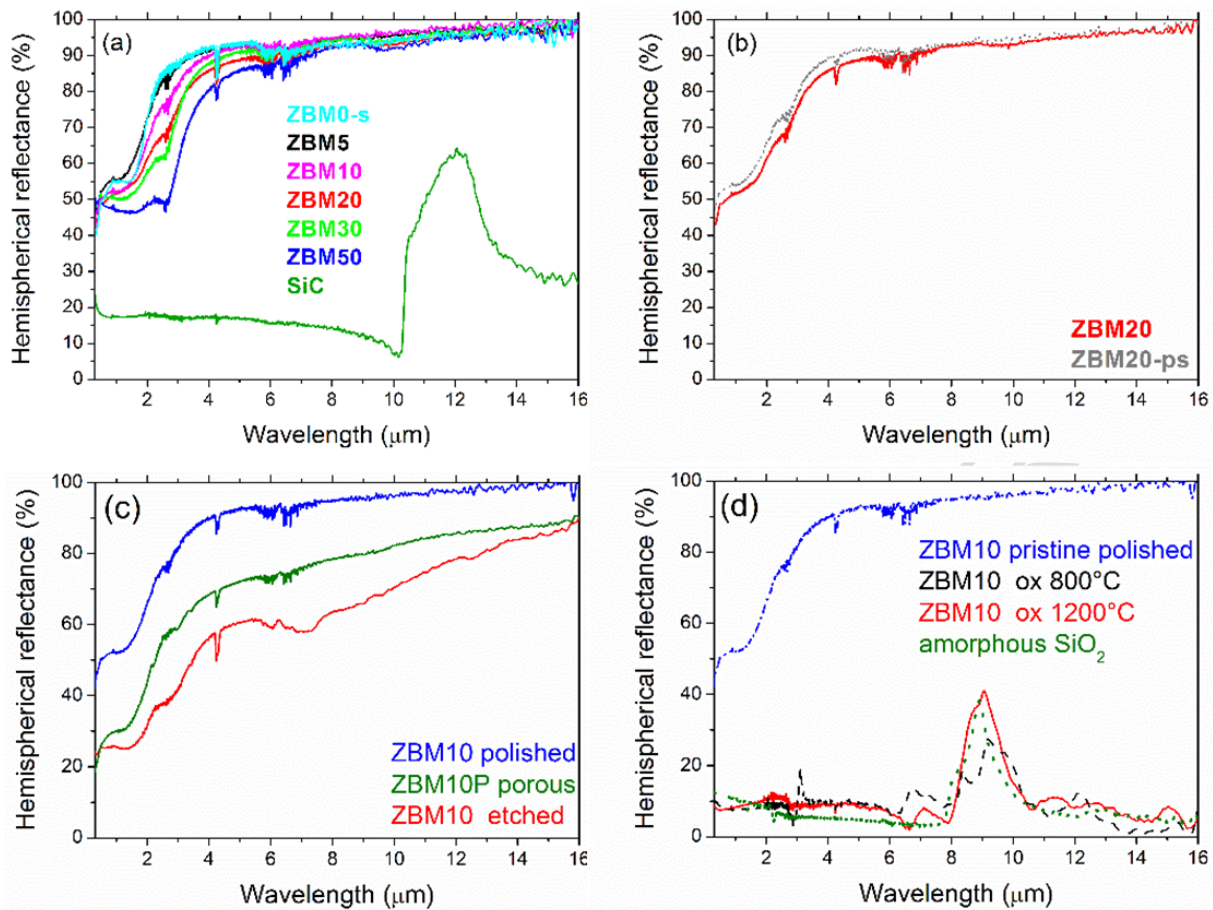
301 In agreement with previous investigations [13,14,16,17,28],  $ZrB_2$  composites have a step-like  
 302 optical behaviour. In this regard, Fig. 6a displays the hemispherical reflectance spectra shown by the  
 303 additive free SPSed sample and the hot pressed ZBMX composites with increasing  $MoSi_2$  content,  
 304 together with that of SiC, reported for the sake of clarity as reference material. We can distinguish  
 305 the typical step-like behaviour of ZBMX samples as well and similar maximum reflectance among  
 306 samples, which is around 85-90%. ZBMX spectra have very similar shape, with the highest values  
 307 for ZBM0-s and ZBM5 especially at short wavelengths. The typical  $MoSi_2$  reflectance minimum at  
 308  $2.7 \mu m$  already appears in the spectrum of ZBM5 and progressively increases proportionally with the  
 309 additive content. The bump at around  $9 \mu m$ , attributable to  $SiO_2$  signal, can be clearly identified only  
 310 in ZBM30 and ZBM50, in agreement with their much higher  $SiO_2$  content than the other hot pressed



311 materials. Completely different spectral characteristics of borides over SiC are well discernible in  
312 Fig. 6a.

313 Fig. 6b evidences that no significant differences in optical spectra can be connected to the  
314 processing technique for ZBM20 samples, either hot pressing and pressureless sintering. Fig. 6c  
315 compares dense and porous ZBM10 obtained by hot pressing (blue and green curves, respectively),  
316 and the dense sample before and after chemical etching (blue and red curves, respectively). Porosity  
317 shows a clear effect in reducing the spectral reflectance with respect to the fully dense sample. On  
318 the other hand, the radical change of surface morphology after chemical etching, inducing an increase  
319 of roughness, also determined a significant decrease of the reflectance over the whole wavelength  
320 examined. This holds particularly true in the intervals of major interest, i.e. for wavelengths lower  
321 than 1  $\mu\text{m}$  and between 1 and 3  $\mu\text{m}$ . In detail, it passes from around 50% in the visible-near IR and  
322 50-80 % in the range 1-3  $\mu\text{m}$  for the polished pristine surface to around 25 % and 25-40 % for the  
323 textured surface in the two investigated ranges (Fig. 6c). As X-ray analyses revealed the presence of  
324 solely  $\text{ZrB}_2$  and  $\text{MoSi}_2$  in the etched sample, the local minimum in the range 6-8  $\mu\text{m}$  in the reflectance  
325 curve of the etched ZBM10 is likely connected to the textured morphology of the surface rather than  
326 to the presence of oxides. In fact, surface texturing has been proved in the literature to strongly affect  
327 optical reflectance properties of solids [31–33].

328 Finally, the optical spectra of the oxidized samples in Fig. 6d result completely changed  
329 compared with the pristine material. Indeed, whilst the XRD are still able to detect  $\text{ZrB}_2$  under the  
330 silica coverage after oxidation at 800°C, the optical spectrum only shows the surficial nature of the  
331 material, e.g. the newly formed silica scale. The spectrum observed in Fig. 6d well compares with  
332 that of amorphous  $\text{SiO}_2$ , as this is the main phase composing the outermost surface scale as discussed  
333 above (Fig. 4b-c). It should be noticed that the same situation is produced upon SiC exposure to high  
334 temperatures in air.



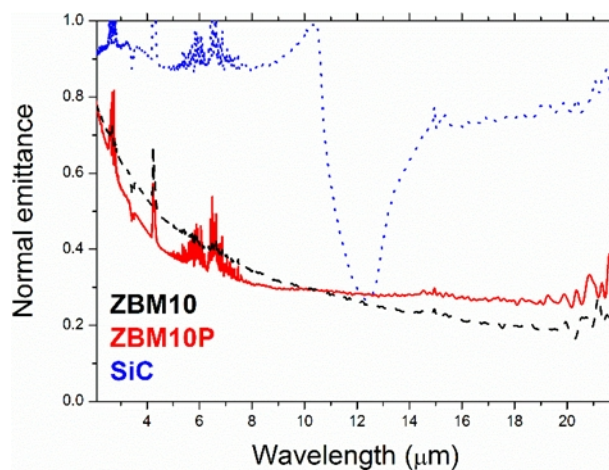
335

336 Fig. 6: a) Comparison of hemispherical reflectance spectra of hot pressed  $ZrB_2$  materials as a function of the additive  
 337 amount. The spectrum of SiC is also shown for reference. b) Comparison between the two samples with 20%  $MoSi_2$  as a  
 338 function of the processing technique. c) Comparison between the spectra of dense, porous and etched ZBM10. d)  
 339 Comparison amongst polished and oxidized ZBM10 samples at 800 or 1200°C, together with that of a reference  
 340 amorphous  $SiO_2$ .

341

342 Experimental emittance spectra at 1100 K of dense and porous samples, ZBM10 and  
 343 ZBM10P, are shown in Fig. 7 and compared to the emittance of a SiC sample. The drop in SiC  
 344 emittance at around 12 μm wavelength is due to intrinsic spectral characteristics of the material (see  
 345 also Fig. 6a) and it represents the Reststrahlen band [34]. Boride spectra are very similar to each other  
 346 and significantly lower than that of SiC. The two ZBM10 spectra cross at around 10 μm wavelength,  
 347 with the dense sample showing a slightly higher spectral curve than the porous one at shorter  
 348 wavelengths. This result at a first glance could seem counter-intuitive. In fact, it could seem  
 349 reasonable to expect a clearly higher thermal emittance of the porous sample than the dense one, as

350 it happens in samples with similar surface roughness or when a denser sample is also smoother  
 351 [35,36]. However it should not be forgotten that thermal emittance is a surface property, thus it is the  
 352 result of the overall balance of all the parameters of the surface. In our case, the samples have a  
 353 different surface finishing. In particular, the dense ZBM10 has a higher roughness than the porous  
 354 ZBM10P pellet. The balance between roughness and porosity effects fairly justifies the observed  
 355 similarity of emittance. Finally, it should be noted, that the small spectral differences outlined above  
 356 do not produce significant differences on the value of the spectrally-integrated emittance ( $\epsilon_{\text{exp}} \approx 0.3$   
 357 for both borides). On the other hand, SiC, which has a roughness similar to that of ZBM10, exhibits  
 358 a markedly higher emittance than borides in the large majority of the spectrum. Accordingly, the  
 359 corresponding integrated value is more than double ( $\epsilon_{\text{exp}} \approx 0.8$ ).



360  
 361 Fig. 7: Comparison of the spectral normal emittance of ZBM10 samples and SiC at 1100 K. Due to thermal contact losses  
 362 at the ceramic pellet/heater interface, 1100K is the maximum temperature actually obtained for these samples. Spectral  
 363 features at around 2.5, 3, 4 and 6  $\mu\text{m}$  wavelength, which are shown by all samples, are instrumental artifacts due to  
 364 unbalanced absorption by air gases.

365

## 366 4. Discussion

### 367 4.1 Bulk and surface features affecting the optical behavior

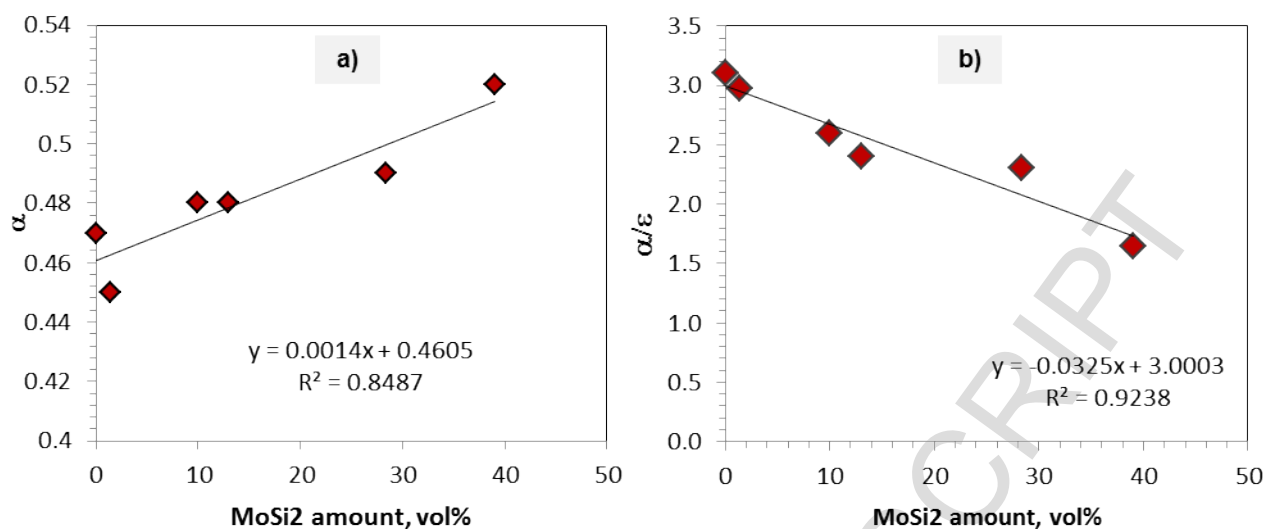
368 One of the main objectives of this work is understanding what are the most important  
 369 microstructural characteristics affecting the optical behaviour. The fundamental parameters we have  
 370 considered are  $\alpha$  and  $\alpha/\epsilon$  that, ideally, should be as closer to one and as higher as possible,

371 respectively. For the sake of comparison, we have indicated the same parameters for a hot pressed  
372 SiC reference material. SiC typical values of  $\alpha$  and  $\alpha/\varepsilon$  are 0.8 and 1, respectively.

373 *Effect of secondary phases:* The experiments conducted indicate that the intrinsic spectral  
374 behaviour of these multiphase materials is affected by the presence of secondary phases such as  
375 MoSi<sub>2</sub>, e.g. by the chemical composition of the final product. To note that the introduction of a  
376 specific sintering agent is often mandatory if we want to exploit the full potential of ZrB<sub>2</sub> as structural  
377 ceramic and improve its oxidation behaviour [20]. For the optical behaviour, we showed that even a  
378 content as low as 5 vol% of MoSi<sub>2</sub> in a ZrB<sub>2</sub> matrix (ZBM5) produces some change in the optical  
379 spectrum, compared to the MoSi<sub>2</sub>-free material (ZBM0-s). Similarly, the presence of silica, in amount  
380 >5 vol% is also detected in the spectra. In the specific case of MoSi<sub>2</sub>, the change of hemispherical  
381 reflectance is observed mostly in the 0.3-3 micron wavelength range, Fig. 6a, but the overall  
382 hemispherical solar absorbance (Eq. 1), plotted in Fig. 8a as a function of MoSi<sub>2</sub> content, just shows  
383 a slight increase from 0.44 to 0.52 for MoSi<sub>2</sub> content increasing from 0 to 50%. This absorbance  
384 increase is beneficial for solar energy application, but  $\alpha$  remains still lower than SiC. On the other  
385 hand, for  $\alpha/\varepsilon$  the variability range lies between 1.7 for ZBM50 and 3.1 for ZBM0-s, Fig. 8b. It clearly  
386 looks that spectral selectivity worsens almost linearly with increasing MoSi<sub>2</sub> and related secondary  
387 phases, like SiO<sub>2</sub>. As term of comparison, it should be recalled that SiC calculated  $\alpha/\varepsilon$  ratio is about  
388 1, which is always lower than all ZBMX products.

389 It is immediate here to notice the dichotomy connected with the decrease of reflectance and its effects  
390 on  $\alpha$  and  $\alpha/\varepsilon$  parameters. In fact, due to spectral properties of UHTCs, it is quite a common result that  
391 a reflectance decrease entails the growth of both  $\alpha$  and  $\varepsilon$  parameters, with a subsequent decrease in  
392  $\alpha/\varepsilon$  ratio. However, some authors underlined the importance of a high absorbance value for spectrally  
393 selective absorbers [5]. Thus, as a phenomenological rule of thumb, providing that the spectral  
394 selectivity is maintained (i.e.  $\alpha/\varepsilon > 1$ ), a higher absorbance should be preferred, even at the cost of  
395 some decrease of spectral selectivity. The spectral selectivity, however, should not be completely  
396 lost, because, as the cited paper proves [5], selective absorbers always show better performances than

397 non-selective materials, even if they are characterized by a high absorbance (e.g. SiC,  $\alpha/\varepsilon=1$ ).



398

399 Fig. 8: a) Solar absorbance,  $\alpha$ , and b) Spectral selectivity,  $\alpha/\varepsilon$ , for the series ZBMX, dense samples.

400

401 *Effect of surface porosity:* Further, surface morphology is the other fundamental parameter  
 402 affecting the optical behavior. We have shown that playing with surface porosity we can achieve a  
 403 drastic change of the optical spectrum. Increase of porosity over 10%, does not substantially change  
 404 the spectrum shape as we still observe the spectral selectivity of the boride phase, but produces a large  
 405 increase of the absorbance. If we use the roughness as a quantitative parameter, we can say that  
 406 variations of at least one order of magnitude in surface roughness result in significant change of  $\alpha$   
 407 and  $\alpha/\varepsilon$ . Therefore, increased roughness leading to improved capability to trap solar radiation could  
 408 be tailored mainly by augmenting the surface porosity. This can be accomplished through addition of  
 409 pore forming agents, with the possibility to decide *a priori* the pore dimensions, or modifying the  
 410 sintering schedule to avoid complete densification.

411 *Effect of surface etching:* If  $\alpha$  and  $\alpha/\varepsilon$  values are concerned, Fig. 9, we can see that surface  
 412 etching increases the absorbance, which is nearly doubled, and decreases the spectral selectivity  
 413 correspondingly, similarly to that obtained in the case of femtosecond-treated materials [31]. It is  
 414 worth to mention that the absorbance value obtained for the etched sample is very similar to that of  
 415 silicon carbide, thus overcoming one of the major criticisms for UHTC materials over SiC itself. On

416 the other hand, the spectral selectivity of etched  $ZrB_2$  remains better. Therefore, these results confirm  
417 that surface texturing is a successful approach for developing promising solar absorbers, according  
418 to the criteria described in [5].

419 *Effect of surface oxidation:* As expected, optical properties of oxidized samples deteriorate  
420 due to the complete change of surface composition and morphology with respect to the pristine  
421 boride, in agreement with the findings of other authors [37]. However, they still remain comparable  
422 to SiC, both in terms of values of the optical parameters and also because, as mentioned before, SiC  
423 itself shows a similar oxidation behavior, with the production of an amorphous silica layer on the  
424 exposed surface.

425 As a final comment about emittance measurements, it is a known effect that the experimental  
426 emittance at high temperature is generally higher than the value estimated from room-temperature  
427 reflectance spectra using Eq. (2) [28]. However, as discussed in the cited work, the parameters  $\alpha$  and  
428  $\alpha/\epsilon$  obtained from the room-temperature optical characterization remain valid if the obtained results  
429 are used for comparison among samples, as the hierarchy and relative differences among specimens  
430 are kept the same, both in low and high temperature measurements.

431

## 432 **4.2 Advantages in the use of UHTC as solar absorbers**

433 The need to identify suitable strategies to halve the cost of energy production from CSP  
434 technologies has fostered research effort aiming at developing materials for alternative, sustainable,  
435 safe and cost-effective energy supply.

436 In this context, innovative materials have been investigated within the SUPERSOLAR  
437 project. In particular, a thorough knowledge of the relationship between processing, microstructure,  
438 thermo-mechanical and optical properties has been assessed for the first time for UHTC materials.  
439 The base properties outlined in this and previous studies [13,14,16,17,28] can be the starting point  
440 for future development of ground-breaking materials with specific properties tunable according to the  
441 needs imposed by the application.

442 The investigations performed so far underlined solar energy relevance as future main energy  
443 supply through the use of UHTCs as innovative materials for solar absorbers. In particular, the  
444 following two aspects have been tackled:

- 445 • Development of new more efficient systems. From the point of view of materials design and  
446 production, particular attention has been devoted to the selection of ceramics of the UHTC class  
447 possessing superior durability and high temperature stability, able to operate at higher  
448 temperatures, as compared to the actual materials based on SiC; appropriate surface treatments  
449 have been also performed to enhance the materials absorbance.
- 450 • Reduction of materials production costs through the employment of cost-effective processing  
451 techniques. In this respect, SHS/SPS and pressureless sintering routes have been also explored  
452 beside the conventional hot pressing technique.

453 In particular, the SHS/SPS approach contemplates several advantages: a possible cost-production  
454 saving could be achieved by the use of raw powders obtained through in-house synthesis; in  
455 addition, SPS has the benefit to reduce the sintering times from the order of hours to minutes. On  
456 the other hand, sintering performed without the application of pressures enables the obtainment  
457 of near-net shape components, thus saving machining costs.

458

### 459 **4.3 Strengths and criticalities of UHTCs as solar absorbers**

460 A clearer picture of the complex relationships amongst process-microstructure-optical  
461 properties of UHTCs can be defined taking advantage of our experience gained in recent years on  
462 this subject [13,14,16,17,28]. In particular, the research activity revealed interesting findings, but also  
463 pointed out some critical issues in the use of UHTCs as solar absorbers.

464 The main strength point is that the optical behaviour of all materials analysed favourably  
465 competes with that of SiC, which is the most widespread material used for current applications. Not  
466 to forget that also the mechanical properties and refractoriness of UHTCs are generally higher than  
467 those of SiC materials, as well. Then, the high thermal conductivity of UHTCs, between 60 and 100

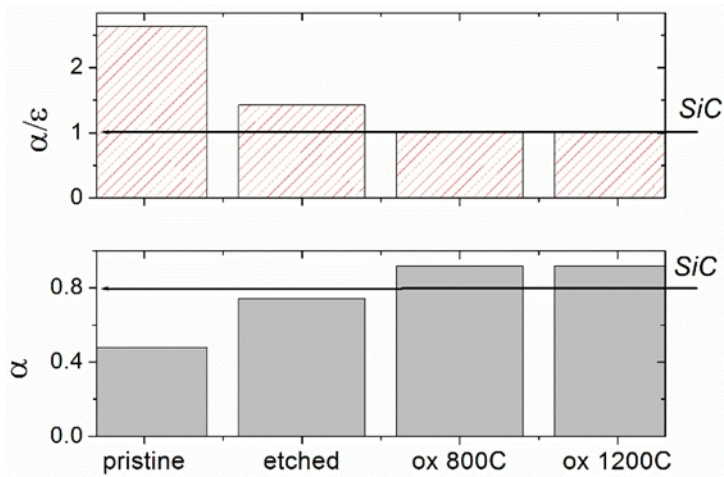
468  $\text{Wm}^{-1} \text{K}^{-1}$  and constant up to  $1500^\circ\text{C}$  [38,39] is even higher than SiC,  $4\text{-}20\text{Wm}^{-1} \text{K}^{-1}$  [40] allowing  
469 for an easy heat transfer of the collected thermal energy to a thermo-convective fluid.

470 Further, the surface treatments experimented in the study, chemical etching and tailored  
471 porosity, proved to effectively decrease the reflectance in the visible-near infrared spectral range, i.e.  
472 increased the ability of the material to absorb the incident radiation, which can be translated in higher  
473 efficiency of the system.

474 One not-negligible problem is related to the cost of the starting powders. UHTC powders are  
475 consistently more expensive than SiC ones. However, in this study we demonstrated the feasibility  
476 of UHTCs starting from in-house reaction synthesized powders, that enabled to save costs as  
477 compared to commercial ones. More important, the maximum temperature required for their  
478 densification is generally lower than that required for commercial UHTC powders, as the SHS  
479 powders are easily sinterable owing to the high defects concentration. One further step towards the  
480 decrease of the sintering temperatures is constituted by the fact that partially porous materials possess  
481 lower reflectance, thanks to an increased absorption capability of the material, as the solar radiation  
482 is more easily trapped into the channels created by porosity.

483 Moving to the critical aspects of the use of UHTCs as solar absorbers for novel high-temperature-  
484 high-efficiency solar plants, the last investigations on the behaviour of oxidized ceramics pointed out  
485 that the transition from boride to oxide, zirconia or silica, has notable impact on the optical response,  
486 see Fig. 6b. This leads to conclude that the use of these materials at high temperature is subordinated  
487 to a protective/reducing environment. However, it is worth to recall that, on a side, SiC also shows  
488 oxidation problems and, on the other side, oxidized borides show  $\alpha/\varepsilon$  values comparable to SiC,  
489 whereas  $\alpha$  parameters are even better than this reference material, see Fig. 9.





490

491 Fig. 9: Spectral selectivity,  $\alpha/\epsilon$ , and solar absorbance,  $\alpha$ , for the pristine and treated samples. Horizontal lines in each plot  
 492 identify the values obtained for SiC.

493

## 494 5. Conclusions

495 The investigations on a broad range of UHTCs allowed to assess that these materials used in  
 496 this novel application as solar absorbers well compare and even overpass the performances of more  
 497 conventional SiC-based materials both at room and high temperatures. Zirconium diboride has been  
 498 taken as case study and thoroughly characterized as a function of starting composition, porosity and  
 499 surface finishing. Surface texturing by chemical etching has been investigated, showing increased  
 500 solar absorbance. Oxidation has shown significantly changed material properties, making borides  
 501 behave more similar to SiC. Finally, thermal optical spectra at 1100 K temperature have been acquired  
 502 and compared to SiC, confirming the trend revealed by room-temperature optical parameters.

503

## 504 Acknowledgements

505 This activity has been carried out in the framework of the FIRB2012-SUPERSOLAR project  
 506 funded by the Italian Ministry of University and Research (Programma “Futuro in Ricerca”, prot.  
 507 RBFR12TIT1). The Italian bank foundation “Fondazione Ente Cassa di Risparmio di Firenze” is  
 508 gratefully acknowledged for supporting a part of this activity within the framework of the SOLE-  
 509 NANO project (pratica n. 2015.0861). Thanks are due Mr. M. Pucci, Mr. M. D’Uva (CNR-INO), Mr.

510 Cesare Melandri (CNR-ISTEC) for technical support and to Mrs. R. Parenti and Mrs. P. Pipino (CNR-  
511 INO) for administrative management.

512

### 513 **References**

- 514 [1] Romero M, Steinfeld A. Concentrating solar thermal power and thermochemical fuels.  
515 Energy Environ Sci 2012;5:9234. doi:10.1039/c2ee21275g.
- 516 [2] Bogaerts WF, Lampert CM. Materials for photothermal solar energy conversion. J Mater Sci  
517 1983;18:2847–75. doi:10.1007/BF00700767.
- 518 [3] Lampert CM. Advanced optical materials for energy efficiency and solar conversion. Sol  
519 Wind Technol 1987;4:347–79. doi:10.1016/0741-983X(87)90067-1.
- 520 [4] Kennedy C. Review of mid-to high-temperature solar selective absorber materials. NREL  
521 Tech Rep 2002:1–58. doi:10.2172/15000706.
- 522 [5] Burlafinger K, Vetter A, Brabec CJ. Maximizing concentrated solar power (CSP) plant  
523 overall efficiencies by using spectral selective absorbers at optimal operation temperatures.  
524 Sol Energy 2015;120:428–38. doi:10.1016/j.solener.2015.07.023.
- 525 [6] Patidar D, Tiwari S, Sharma PK, Chandra L, Shekhar R. Open Volumetric Air Receiver  
526 Based Solar Convective Aluminum Heat Treatment Furnace System. Energy Procedia, vol.  
527 69, 2015, p. 506–17. doi:10.1016/j.egypro.2015.03.059.
- 528 [7] Srivastva U, Malhotra RK, Kaushik SC. Recent Developments in Heat Transfer Fluids Used  
529 for Solar Thermal Energy Applications. J Fundam Renew Energy Appl 2015;5.  
530 doi:10.4172/20904541.1000189.
- 531 [8] Stadler H, Tiddens A, Schwarzbözl P, Göhring F, Baumann T, Trautner J. Improved  
532 performance of open volumetric receivers by employing an external air return system. Sol  
533 Energy 2017;155:1157–64. doi:10.1016/j.solener.2017.07.050.
- 534 [9] Zhu G, Libby C. Review and future perspective of central receiver design and performance.  
535 AIP Conf. Proc., vol. 1850, 2017. doi:10.1063/1.4984395.

- 536 [10] Wuchina EJ, Opila E, Opeka M, Fahrenholtz WG, Talmy I. UHTCs: Ultra-high temperature  
537 ceramic materials for extreme environment applications. *Electrochem Soc Interfaces*  
538 2007;16:30–6.
- 539 [11] Silvestroni L, Kleebe H-J, Fahrenholtz WG, Watts J. Super-strong materials for temperatures  
540 exceeding 2000 °C. *Sci Rep* 2017;7:40730. doi:doi:10.1038/srep40730.
- 541 [12] Fahrenholtz WG, Wuchina EJ, Lee WE, Y. Z, editors. *Ultra-High Temperature Ceramics:*  
542 *Materials for Extreme Environment Applications*. John Wiley & Sons; 2014.
- 543 [13] Sani E, Mercatelli L, Meucci M, Balbo A, Silvestroni L, Sciti D. Compositional dependence  
544 of optical properties of zirconium, hafnium and tantalum carbides for solar absorber  
545 applications. *Sol Energy* 2016;131:199–207. doi:10.1016/j.solener.2016.02.045.
- 546 [14] Sani E, Mercatelli L, Meucci M, Silvestroni L, Balbo A, Sciti D. Process and composition  
547 dependence of optical properties of zirconium, hafnium and tantalum borides for solar  
548 receiver applications. *Sol Energy Mater Sol Cells* 2016;155:368–77.  
549 doi:10.1016/j.solmat.2016.06.028.
- 550 [15] Musa C, Licheri R, Orrù R, Cao G, Sciti D, Silvestroni L, et al. Processing, mechanical and  
551 optical properties of additive-free ZrC ceramics prepared by Spark Plasma Sintering.  
552 *Materials (Basel)* 2016;9. doi:10.3390/ma9060489.
- 553 [16] Sani E, Mercatelli L, Meucci M, Balbo A, Musa C, Licheri R, et al. Optical properties of  
554 dense zirconium and tantalum diborides for solar thermal absorbers. *Renew Energy*  
555 2016;91:340–6. doi:10.1016/j.renene.2016.01.068.
- 556 [17] Sani E, Meucci M, Mercatelli L, Balbo A, Musa C, Licheri R, et al. Titanium diboride  
557 ceramics for solar thermal absorbers. *Sol Energy Mater Sol Cells* 2017;169:313–9.  
558 doi:10.1016/j.solmat.2017.05.038.
- 559 [18] Sani E, Mercatelli L, Meucci M, Zoli L, Sciti D. Lanthanum hexaboride for solar energy  
560 applications. *Sci Rep* 2017:1–7. doi:10.1038/s41598-017-00749-w.
- 561 [19] Rousseau B, Guevelou S, Vicente J, Caliot C, Flamant G. Tuning the Spectral Selectivity of

- 562 Sic-Based Volumetric Solar Receivers With Ultra-High Temperature Ceramic Coatings.  
563 Ceram. Energy Conversion, Storage, Distrib. Syst., vol. 255, 2016, p. 227–38.  
564 doi:10.1002/9781119234531.ch21.
- 565 [20] Sciti D, Silvestroni L, Medri V, Monteverde F. Sintering and Densification Mechanisms of  
566 Ultra-High Temperature Ceramics. 2014. doi:10.1002/9781118700853.ch6.
- 567 [21] Neuman EW, Hilmas GE, Fahrenholtz WG. Processing, microstructure, and mechanical  
568 properties of zirconium diboride-boron carbide ceramics. Ceram Int 2017;43:6942–8.  
569 doi:10.1016/j.ceramint.2017.02.117.
- 570 [22] Neuman EW, Hilmas GE, Fahrenholtz WG. Processing, microstructure, and mechanical  
571 properties of large-grained zirconium diboride ceramics. Mater Sci Eng A 2016;670:196–  
572 204. doi:10.1016/j.msea.2016.06.017.
- 573 [23] Farahbakhsh I, Ahmadi Z, Shahedi Asl M. Densification, microstructure and mechanical  
574 properties of hot pressed ZrB<sub>2</sub>–SiC ceramic doped with nano-sized carbon black. Ceram Int  
575 2017;43:8411–7. doi:10.1016/j.ceramint.2017.03.188.
- 576 [24] Neuman EW, Hilmas GE, Fahrenholtz WG. Mechanical behavior of zirconium diboride-  
577 silicon carbide-boron carbide ceramics up to 2200°C. J Eur Ceram Soc 2015;35:463–76.  
578 doi:10.1016/j.jeurceramsoc.2014.09.021.
- 579 [25] Petrovic JJ. Mechanical behavior of MoSi<sub>2</sub> and MoSi<sub>2</sub> composites. Mater Sci Eng A  
580 1995;192–193:31–7. doi:10.1016/0921-5093(94)03246-7.
- 581 [26] Sciti D, Silvestroni L, Saccone G, Alfano D. Effect of different sintering aids on thermo-  
582 mechanical properties and oxidation of SiC fibers - Reinforced ZrB<sub>2</sub> composites. Mater  
583 Chem Phys 2013;137:834–42. doi:10.1016/j.matchemphys.2012.09.071.
- 584 [27] Licheri R, Musa C, Orrù R, Cao G, Sciti D, Silvestroni L. Bulk monolithic zirconium and  
585 tantalum diborides by reactive and non-reactive spark plasma sintering. J Alloys Compd  
586 2016;663:351–9. doi:10.1016/j.jallcom.2015.12.096.
- 587 [28] Mercatelli L, Meucci M, Sani E. Facility for assessing spectral normal emittance of solid

- 588 materials at high temperature. *Appl Opt* 2015;54:8700. doi:10.1364/AO.54.008700.
- 589 [29] ASTM G173-03(2012), Standard Tables for Reference Solar Spectral Irradiances: Direct  
590 Normal and Hemispherical on 37° Tilted Surface, ASTM International, West Conshohocken,  
591 PA, 2012, www.astm.org n.d. doi:DOI: 10.1520/G0173-03R12.
- 592 [30] Leach R. Characterisation of areal surface texture. vol. 9783642364. 2013. doi:10.1007/978-  
593 3-642-36458-7.
- 594 [31] Sciti D, Silvestroni L, Trucchi DM, Cappelli E, Orlando S, Sani E. Femtosecond laser  
595 treatments to tailor the optical properties of hafnium carbide for solar applications. *Sol*  
596 *Energy Mater Sol Cells* 2015;132. doi:10.1016/j.solmat.2014.09.037.
- 597 [32] Nayak BK, Iyengar V V., Gupta MC. Efficient light trapping in silicon solar cells by  
598 ultrafast-laser-induced self-assembled micro/nano structures. *Prog Photovoltaics Res Appl*  
599 2011;19:631–9. doi:10.1002/pip.1067.
- 600 [33] King DL, Buck ME. Experimental optimization of an anisotropic etching process for random  
601 texturization of silicon solar cells. *Conf Rec Twenty-Second IEEE Photovolt Spec Conf -*  
602 1991 1991:303–8. doi:10.1109/PVSC.1991.169228.
- 603 [34] Huffmann B and. Absorption and scattering of light by small particles. WILEY-VCH Verlag  
604 GmbH & Co. KGaA; 1998. doi:10.1002/9783527618156.
- 605 [35] Sani E, Mercatelli L, Sans JL, Silvestroni L, Sciti D. Porous and dense hafnium and  
606 zirconium ultra-high temperature ceramics for solar receivers. *Opt Mater (Amst)*  
607 2013;36:163–8. doi:10.1016/j.optmat.2013.08.020.
- 608 [36] Sciti D, Silvestroni L, Sans JL, Mercatelli L, Meucci M, Sani E. Tantalum diboride-based  
609 ceramics for bulk solar absorbers. *Sol Energy Mater Sol Cells* 2014;130:208–16.  
610 doi:10.1016/j.solmat.2014.07.012.
- 611 [37] Charpentier L, Caliot C. The impact of the oxidation on the optical properties of TaC. *Sol*  
612 *Energy Mater Sol Cells* 2017;171:16–23. doi:10.1016/j.solmat.2017.06.019.
- 613 [38] Zimmermann JW, Hilmas GE, Fahrenholtz WG, Dinwiddie RB, Porter WD, Wang H.

- 614 Thermophysical properties of ZrB<sub>2</sub> and ZrB<sub>2</sub>-SiC ceramics. J Am Ceram Soc  
615 2008;91:1405–11. doi:10.1111/j.1551-2916.2008.02268.x.
- 616 [39] Guo S-Q. Densification of ZrB<sub>2</sub>-based composites and their mechanical and physical  
617 properties: A review. J Eur Ceram Soc 2009;29:995–1011.  
618 doi:10.1016/j.jeurceramsoc.2008.11.008.
- 619 [40] Levinshtein ME, Rumyantsev SL, Shur M, Bougrov V, Zubrilov A. Properties of Advanced  
620 Semiconductor Materials: GaN, AlN, InN, BN, SiC, SiGe. 2001. doi:citeulike-article-  
621 id:6144117.
- 622
- 623

624 **Tables**

Label	MoSi <sub>2</sub> vol%	Sintering technique	T,t,P °C, min, MPa	Bulk relative density %	Surface porosity vol%	Mean pore size µm	Mean g.s. µm	Max g.s. µm	Min g.s. µm	Secondary phases by SEM-EDS vol%
ZBM0-s	0	SPS	1850,20,60	>96	~4	4.90	19±6	33.5	8.5	-
ZBM5	5	HP	1900,10,30	>98	~2	0.13	1.9±0.7	3.6	0.9	1.4 MoSi <sub>2</sub> , 1.5 SiO <sub>2</sub> /SiC
ZBM10	10	HP	1850,10,30	>96	~4	0.13	2.4±0.6	3.9	1.4	8.5 MoSi <sub>2</sub> , 1.4 SiO <sub>2</sub> , 0.7 SiC
ZBM20	20	HP	1800,4,30	>98	~2	0.10	2.4±0.9	5.4	0.6	13 MoSi <sub>2</sub> , 2.5 SiO <sub>2</sub> , 2.0 SiC, 0.7 ZrO <sub>2</sub> , 0.6 MoB
ZBM30	30	HP	1850,3,30	>98	~2	0.10	1.7±0.6	3.6	0.6	28.4 MoSi <sub>2</sub> , 3.4 SiO <sub>2</sub> /SiC
ZBM50	50	HP	1750,13,30	>98	~2	0.10	1.9±0.8	4.3	0.7	39 MoSi <sub>2</sub> , 6.5 SiO <sub>2</sub> , 2 MoB, 1 ZrO <sub>2</sub> , 1 SiC
ZBM20-ps	20	PS	1950,60,-	>98	~2	1.45	2.6±0.7	1.3	4.1	18 MoSi <sub>2</sub> , 2 MoB, 0.5 SiO <sub>2</sub>
ZBM10P	10	PS	1950,60,-	~87	~13	4.70	2.8±0.7	5.2	1.2	8 MoSi <sub>2</sub> , 2 MoB

625

626 Table I: Composition, sintering technique and parameters, T: maximum temperature, t: dwell at T, P: applied pressure,  
627 relative density, porosity features, mean, maximum and minimum grain size (g.s.) and secondary phases of the ZrB<sub>2</sub>-  
628 based materials. Porosity is estimated by image analysis. SPS: spark plasma sintering, HP: hot pressing, PS: pressureless  
629 sintering.

630

	Polished							Porous	Etched	Oxidised	
	ZBM0-s	ZBM5	ZBM10	ZBM20	ZBM30	ZBM50	ZBM20-ps	ZBM10-P	ZBM Etc	ZBM 800	ZBM 1200
<i>Sq</i> ( $\mu\text{m}$ )	0.44±0.10	(68±4)·10 <sup>-3</sup>	(34±3)·10 <sup>-3</sup>	(12±3)·10 <sup>-3</sup>	(16±1)·10 <sup>-3</sup>	(22±1)·10 <sup>-3</sup>	(37±10)·10 <sup>-3</sup>	1.72±0.02	0.69±0.01	0.5±0.3	5.6±4.3
<i>Ssk</i>	-7.1±1.1	-2.4±0.7	-1.2±0.5	-4.5±2.1	-3.8±0.4	-6.1±1.6	-6.7±1.2	-4.3±0.1	-0.7±0.1	0.9±2.4	1.1±0.9
<i>Sku</i>	83±15	12±4	8±3	81±60	36±5	80±40	97±28	16.3±0.6	3.3±0.6	29±12	5.9±1.6
<i>Sp</i> ( $\mu\text{m}$ )	0.8±0.1	5.9±3.5	0.27±0.01	0.21±0.15	0.21±0.01	0.21±0.01	0.28±0.01	8.4±2.9	3.0±1.7	9.8±2.6	46±33
<i>Sv</i> ( $\mu\text{m}$ )	9.6±2.5	4.1±2.7	0.51±0.18	0.63±0.46	0.44±0.04	0.70±0.20	1.47±0.74	25.3±0.2	5.5±1.5	9.3±10	11.6±1.1
<i>Sz</i> ( $\mu\text{m}$ )	10.4±2.7	10.1±3.1	0.8±0.2	0.8±0.6	0.66±0.04	0.9±0.2	1.8±0.7	33.6±3.3	8.5±3.1	19.1±8.8	57±34
<i>Sa</i> ( $\mu\text{m}$ )	0.21±0.28	(33±4)·10 <sup>-3</sup>	(25±2)·10 <sup>-3</sup>	(8±2)·10 <sup>-3</sup>	(100±1)·10 <sup>-4</sup>	(12±1)·10 <sup>-3</sup>	(17±4)·10 <sup>-3</sup>	1.16±0.01	0.57±0.01	0.36±0.18	4.2±3.2

631

632 Table II: Measured average values and standard deviation of 3D surface texture parameters of the polished and textured  
633 (porous/etched/oxidized) ZrB<sub>2</sub>-based composites.

634



635 **Figures captions**

636 Fig. 1: SEM images of the surface of various  $ZrB_2$ -based ceramics showing different microstructural features. a) ZBM0-s  
637 by SHS/SPS, b) ZBM20-ps by pressureless sintering; c) ZBM10 by HP and d) porous ZBM10P by pressureless sintering  
638 in presence of pore-generating agent. Pores are marked with dotted circles.

639  
640 Fig. 2: SEM images of the polished surfaces of hot pressed  $ZrB_2$ -based composites with increasing  $MoSi_2$  amount: a) 5  
641 vol%, b) 20 vol%, c) 30 vol% and d) 50 vol%.

642  
643 Fig. 3: a)-b) SEM images of the chemically etched surface of ZBM10 with corresponding EDS spectra in c).

644  
645 Fig. 4: a) X-ray diffraction patterns of ZBM10 upon exposure to oxidizing environment at 800°C and 1200°C for 10 hours  
646 and corresponding SEM images of the external surface oxidized at b)-d) at 800°C and e)-g) 1200°C. d) and g) are  
647 magnified images of the boxed areas in c) and f), respectively.

648  
649 Fig. 5: Topographic maps of the ZBM10 sample upon different surface finishing a) as-polished, b) chemically etched  
650 (ZBMetc), c) oxidized at 800°C (ZBM800) and d) oxidised at 1200°C (ZBM1200) for 10 hours.

651  
652 Fig. 6: a) Comparison of hemispherical reflectance spectra of hot pressed  $ZrB_2$  materials as a function of the additive  
653 amount. The spectrum of SiC is also shown for reference. b) Comparison between the two samples with 20%  $MoSi_2$  as a  
654 function of the processing technique. c) Comparison between the spectra of dense, porous and etched ZBM10. d)  
655 Comparison amongst polished and oxidized ZBM10 samples at 800 or 1200°C, together with that of a reference  
656 amorphous  $SiO_2$ .

657  
658 Fig.7: Comparison of the spectral normal emittance of ZBM10 samples and SiC at 1100 K. Due to thermal contact losses  
659 at the ceramic pellet/heater interface, 1100K is the maximum temperature actually obtained for these samples. Spectral  
660 features at around 2.5, 3, 4 and 6  $\mu m$  wavelength, which are shown by all samples, are instrumental artifacts due to  
661 unbalanced absorption by air gases.

662  
663 Fig. 8: a) Solar absorbance,  $\alpha$ , and b) Spectral selectivity,  $\alpha/\epsilon$ , for the series ZBMX, dense samples.

664

665 Fig. 9: Spectral selectivity,  $\alpha/\varepsilon$ , and solar absorbance,  $\alpha$ , for the pristine and treated samples. Horizontal lines in each plot  
666 identify the values obtained for SiC.

ACCEPTED MANUSCRIPT

### Highlights

- Effect of microstructure and finishing on the optical properties of diverse ZrB<sub>2</sub> materials
- Surface texturing by chemical etching led to higher solar absorbance and efficiency
- Oxidation significantly changes the borides properties which behave similar to SiC
- Superior durability and temperature stability enables UHTCs to operate above 500°C
- UHTCs performances in solar absorbers overpass SiC-based materials ones